



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C		
601/	120mΩ @ V _{GS} = 10V	4.4A		
60V	180mΩ @ V _{GS} = 4.5V	3.5A		

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control
- Uninterrupted power supplies

Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

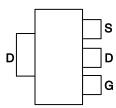
Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.112 grams (Approximate)

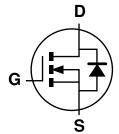
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A11GTA	See below	7	12	1,000

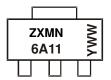
Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

SOT223 (Type DN)



ZXMN6A11 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2= 2022) WW or $\overline{W}W = Week Code (01~53)$

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage	Drain-Source Voltage			60	V	
Gate-Source Voltage			V _{GS}	±20		
Continuous Drain Current	V _{GS} = 10V	(Note 6) T _A = +70°C (Note 6) (Note 5)	I _D	4.4 3.5 3.1		
Pulsed Drain Current	$V_{GS} = 10V$	(Note 7)	I _{DM}	15.6	А	
Continuous Source Current (Body Diode) (Note 6)		I _S	4.4			
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	15.6			

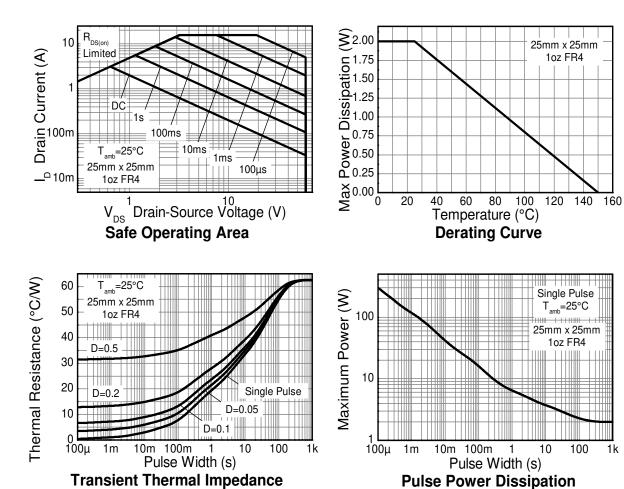
Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		2.0 16	w	
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	D	62.5		
Thermal nesistance, Junction to Ambient	(Note 6)	── R _{eJA}	32.0	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	R ₀ JL	9.8		
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C		

- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as Note 5, except the device is measured at t ≤ 10 seconds.
- Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300μs.
 Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

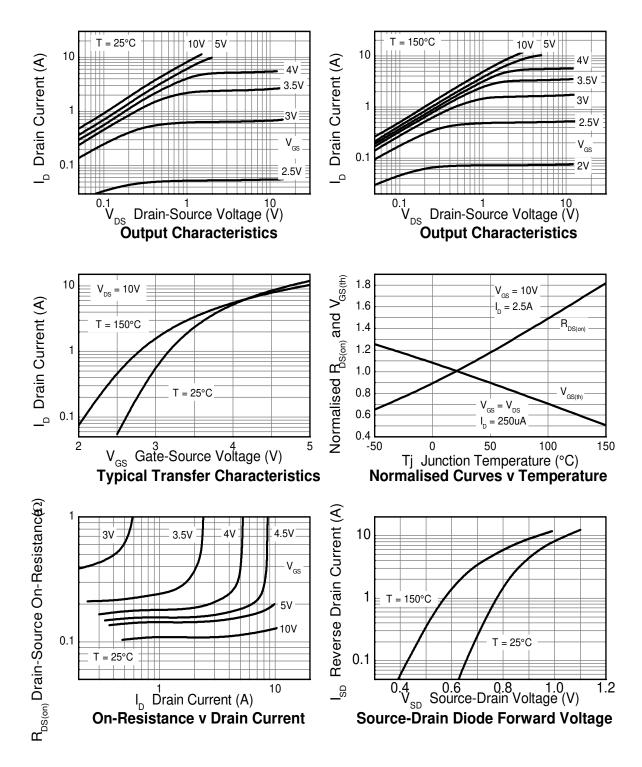
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS					•		
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS}$; = 0V
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{D}$	os = 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$I_D = 250 \mu A, V_{DS}$	$s = V_{GS}$
Static Drain Source On Registence (Note 6)		_	0.105	0.120	Ω	V _{GS} = 10V, I _D = 2.5A	
Static Drain-Source On-Resistance (Note 6)	R _{DS(on)}	_	0.150	0.180	Ω	$V_{GS} = 4.5V, I_{D} =$	= 2A
Forward Transconductance (Notes 6 & 7)	g _{fs}	_	4.9	_	S	$V_{DS} = 15V, I_{D} =$	2.5A
Diode Forward Voltage (Note 6)	V _{SD}	_	0.85	0.95	V	I _S = 2.8A, V _{GS} =	= 0V, T _J = +25°C
Reverse Recovery Time (Note 7)	t _{rr}	_	21.5	_	ns	I _S = 2.8A, di/dt = 100A/μs T _J = +25°C	
Reverse Recovery Charge (Note 7)	Q _{rr}	_	20.5	_	nC		
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	330	_		101/11	0) /
Output Capacitance	Coss	_	35.2	_	рF	$V_{DS} = 40V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	17.1	_		I = 1.0IVIDZ	
Gate Charge (Note 8)	Q_{g}	_	3.0	_		$V_{GS} = 4.5V$	
Total Gate Charge (Note 8)	Qg	_	5.7	_	nC		V _{DS} = 15V
Gate-Source Charge (Note 8)	Qgs	_	1.25	_	110	$V_{GS} = 10V$ I_{D}	$I_D = 2.5A$
Gate-Drain Charge (Note 8)	Q_{gd}	_	0.86	_			
Turn-On Delay Time (Note 8)	t _{D(on)}	_	1.95	_	$N_{DD} = 30 \text{V}, \ I_D = 2.5 \text{A}, \ R_G = 6 \Omega, \ V_{GS} = 10 \text{V}$		
Turn-On Rise Time (Note 8)	t _r	_	3.5	_			2.5A,
Turn-Off Delay Time (Note 8)	t _{D(off)}	_	8.2	_			: 10V
Turn-Off Fall Time (Note 8)	t _f	_	4.6	_			

Notes:

^{6.} Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
7. For design aid only, not subject to production testing.
8. Switching characteristics are independent of operating junction temperature.

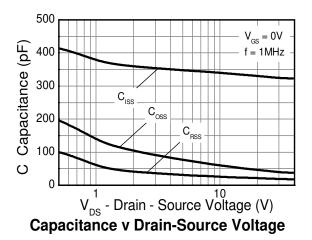


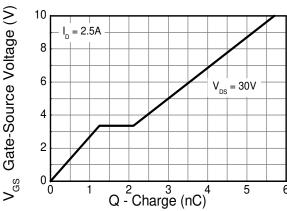
Typical Characteristics





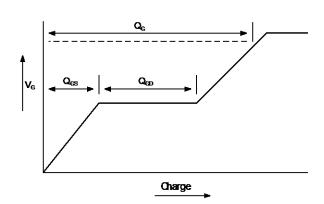
Typical Characteristics (continued)





Gate-Source Voltage v Gate Charge

Test Circuit



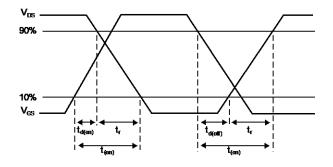
Ourrent regulator

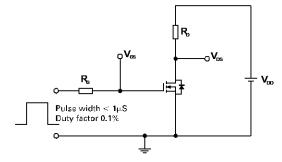
12V 0.2µF 50k Same as DUT

V_{cs} DUT

Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

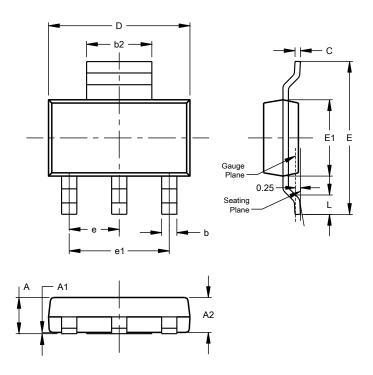
Switching time test circuit



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

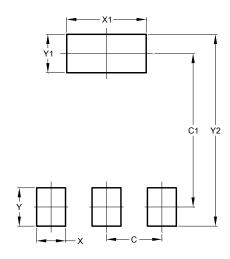


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A 1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
Ĺ	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
V2	8 00		



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